

AMENDMENTS TO THE CLAIMS

Please amend claims 1-7 and 9-11, such that the status of the claims is as follows:

1. (Currently Amended) A field effect transistor sandwiched organic semiconductor, comprising:
 - a substrate (1).
 - a gate electrode (2) formed on the surface of the substrate (1),
 - a gate insulation layer (3) formed on the substrate (1) and the gate electrode (2),
 - which is characterized in that, further comprising:
 - an organic active layer (4) formed on the gate insulation layer (3), or meanwhile leaving a part of the gate insulation layer (3) to be exposed,
 - a source and drain electrodes (5) formed on a part of the gate insulation layer (3) and a part of the organic active layer (4),
 - an active layer (6) formed on the exposed part of the gate insulation layer (3), the organic active layer (4), the source electrode and the drain electrode (5).
2. (Currently amended) The field effect transistor according to claim 1, wherein the ~~said~~ organic active layer (4) has holes.
3. (Currently amended) The field effect transistor according to claim 2, wherein ~~the~~ the semiconductor ~~material~~ is an organic semiconductor material or a hybridized product of organic material and inorganic material.
4. (Currently amended) The field effect transistor according to claim 3, wherein the ~~said~~ organic semiconductor material is a solid-state material formed by mixing, eutecting or laminating of two or more kinds of molecular material.

5. (Currently amended) The field effect transistor according to claim 4, wherein the ~~said~~ organic semiconductor material has a carrier mobility of at least $10^{-3}\text{cm}^2/\text{V.s.}$

6. (Currently amended) The field effect transistor according to claim 1, wherein a semiconductor material for the organic active layer (4) is the same as that for the active layer (6).

7. (Currently amended) The field effect transistor according to claim 1, wherein a semiconductor material for the organic active layer (4) is different from that for the active layer (6).

8. (Previously presented) The field effect transistor according to claim 1, wherein a semiconductor material for the active layers (4) and (6) is eutectic.

9. (Currently amended) The field effect transistor according to claim 1, wherein the ~~said~~ active layers (4) and (6) are comprised of at least one selected from a group consisting of CuPc, NiPc, ZnPc, H₂Pc, TiOPc, VOPc, F₁₆CuPc, F₁₆ZnPc and Pentacene, respectively.

10. (Currently amended) The field effect transistor according to claim 1, wherein the ~~said~~ organic active layer (4) is comprised of at least one selected from a group consisting of CuPc, NiPc, ZnPc, H₂Pc, F₁₆CuPc, F₁₆ZnPc and Pentacene, and the said active layer (6) is comprised of at least one selected from a group consisting of twin-Pc metal, H₂Nc, CoNc, CuNc, ZnNc and NiNc.

11. (Currently amended) The field effect transistor according to claim 10, wherein the ~~said~~ twin-Pc metal is at least one selected from a group consisting of LaPc₂, CePc₂, PrPc₂, NdPc₂, SmPc₂, EuPc₂, GdPc₂, TbPc₂, DyPc₂, HoPc₂, ErPc₂, TmPc₂, YbPc₂, LuPc₂, YPc₂, ZrPc₂, HfPc₂ and SnPc₂.

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12. (Canceled)